We claim:

- 1. A composition suitable for cleaning, etching and dissolving alkaline earth metal fluoride crystals and optical elements made therefrom, said composition comprising a mineral acid and a fluoride ion sequestering agent.
- 2. The composition according to claims 1, wherein the mineral acid is selected from the group consisting of concentrated nitric acid, concentrated perchloric acid and concentrated hydrochloric acid.
- 3. The composition according to claim1 wherein the fluoride ion sequestering agent is selected from the group consisting of boric acid, hypophosphorus acid and metaphosphoric acid.
- 4. The composition according to claim1, wherein the mineral acid is concentrated nitric acid and the sequestering agent is boric acid.
- 5. The composition according to claim 1, wherein the concentration of the fluoride ion sequestering agent is in the range of 1-5.6% w/v.
- 6. The composition according to claim 4, wherein the concentration of the fluoride ion sequestering agent is in the range of 1-5.6% w/v.

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7. A method of making a single crystal of an alkaline earth metal fluoride suitable for use in making <200nm optical elements, the method comprising the steps of:

providing an aqueous cleaning/etching composition comprised of a mineral acid and a fluoride ion sequestering agent;

providing an alkaline earth metal fluoride seed crystal;

cleaning/etching the fluoride seed crystal with the cleaning/etching solution and removing boron residues by washing with a dilute hydrofluoric acid solution;

providing a crucible suitable for growing metal fluoride crystals, the crucible having a reservoir at its bottom for receiving the seed crystal;

inserting the seed crystal into the reservoir wherein the cleaned and etched crystal is oriented along a selected orientation;

charging the crucible with a metal fluoride feed stock;

placing the charged crucible into a furnace suitable for growing metal fluoride crystals and heating the crucible containing the feedstock to melt the feedstock and the top part of the seed crystal; and

slowing cooling the melt so as to grow an oriented alkaline earth metal fluoride crystal having an <200 nm internal transmission of at least 90%/cm.

- 8. The method according to claim 7, wherein the cleaning/etching solution is comprised of:
 - (a) one part concentrated mineral acid and
- (b) 0.5-7 parts a solution of a fluoride ion sequestering agent, wherein the sequestering agent is present in the solution at a concentration in the range of 3-7% wt./vol.
- 9. The method according to claim 8, wherein the sequestering agent is boric acid and the mineral acid is concentrated nitric acid.
- 10. The method according to claim 7, wherein the cleaning/etching is conducted at a temperature in the range of 30-175 °C for a time in the range of 30 minutes to 48 hours depending on the alkaline earth metal fluoride undergoing cleaning/etching, the temperature being greater and/or the time being longer in the order $MgF_2 > CaF_2 > BaF_2$.
- 11. A method of dissolving a single crystal of an alkaline earth metal fluoride or fragments thereof, the method comprising the steps of:

providing an aqueous alkaline earth metal fluoride dissolving solution comprised of a mineral acid and a fluoride ion sequestering agent;

providing an alkaline earth metal fluoride crystal or fragments thereof; dissolving said metal fluoride crystal or fragments thereof in said dissolving composition.

- 12. The method according to claim 11, wherein the dissolving solution is comprised of:
 - (a) one part concentrated mineral acid and
- (b) 0.5-7 parts a solution of a fluoride ion sequestering agent, wherein the sequestering agent is present in the solution at a concentration in the range of 3-7% wt./vol.

- 13. The method according to claim 8, wherein the sequestering agent is boric acid and the mineral acid is concentrated nitric acid.
- 14. The method according to claim 11, wherein the dissolving is conducted at a temperature in the range of 50-250 °C for a time in the range of 1 hour to 5 days depending on the alkaline earth metal fluoride undergoing cleaning/etching, the temperature being greater and/or the time being longer in the order $MgF_2 > CaF_2 > BaF_2$.